2SK3048

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low on-resistance
- No secondary breakdown

Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25$ °C

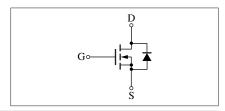
Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V _{DSS}	600	V	
Gate-source surrender voltage	V _{GSS}	±30	V	
Drain current	I_{D}	±3	A	
Peak drain current	I_{DP}	±6	A	
Avalanche energy capability *	EAS	22.5	mJ	
Power dissipation	P_{D}	35	W	
$T_a = 25^{\circ}C$		2		
Channel temperature	T _{ch}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	

Note) *: L = 5 mH, $I_L = 3$ A, 1 pulse

Unit: mm 4.6±0.2 9.9±0.3 2.9±0.2 φ 3.2±0.1 15.0±0.5 1.4±0.2 2.6±0.1 1.6+0.2 13.7±0.2 0.55±0.15 5.08±0.50 1: Gate 2: Drain 3: Source TO-220D-A1 Package

Marking Symbol: K3048

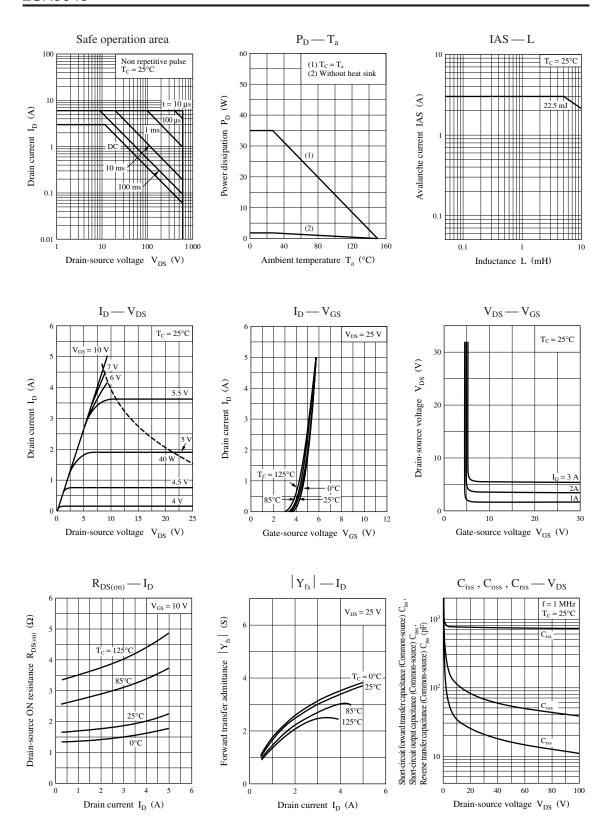
Internal Connection



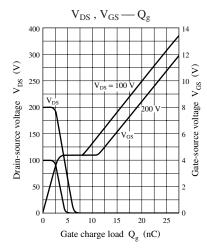
■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

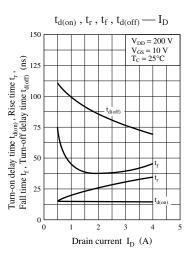
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 480 \text{ V}, V_{GS} = 0$			100	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$			±1	μΑ
Gate threshold voltage	V _{th}	$V_{DS} = 25 \text{ V}, I_{D} = 1 \text{ mA}$	2.0		5.0	V
Forward transfer admittance	Yfs	$V_{DS} = 25 \text{ V}, I_{D} = 2 \text{ A}$	1.5	2.5		S
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$		1.7	2.5	Ω
Diode forward voltage	V_{DF}	$I_{DR} = 3 \text{ A}, V_{GS} = 0$			-1.5	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		750		pF
Short-circuit output capacitance (Common source)	C _{oss}			80		pF
Reverse transfer capacitance (Common source)	C _{rss}			25		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 200 \text{ V}, I_D = 2 \text{ A}, R_L = 100 \Omega$		15		ns
Rise time	t _r	$V_{GS} = 10 \text{ V}$		25		ns
Fall time	$t_{\rm f}$			40		ns
Turn-off delay time	t _{d(off)}			90		ns
Thermal resistance (ch-c)	R _{th(ch-c)}				3.5	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				62.5	°C/W

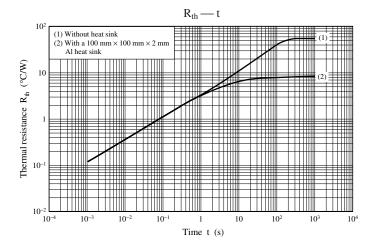
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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